Optimal SIC substrates for Integrated Microwave and Power Circuits

Results

Project information

**OSIRIS**

Grant agreement ID: 662322

[Project website](#)

Status: Closed project

Start date: 1 May 2015

End date: 30 November 2018

Funded under: H2020-EU.2.1.1.7.

Overall budget: € 4,487,117,50

EU contribution: € 1,819,212

Coordinated by: III-V LAB France

Deliverables

Websites, patent filings, videos etc. (7)

*Newsletter 1*

*Project website*

Workshop on material research

Workshop on devices and applications

*Newsletter 2*
**Publications**

Documents, reports (1)

**Report thermal conductivity of substrates and epiwafers**
LIU will report on the thermal conductivity of the different substrates and epiwafers used in the project

Conference proceedings (5)

**Surface properties of AlInN/GaN heterostructures**
*Author(s):* A. Minj, D. Skuridina, D. Cavalcoli, A. Cros, P. Vogt, M. Kneissl, H. Ben Ammar and P. Ruterana
*Published in:* E-MRS, Issue Spring meeting, 2-6 May 2016 Lille France, 2016

**Results on specific backside opening process dedicated to engineering package for SiC component**
*Author(s):* G. Bascoul, F. Infante
*Published in:* Association d'analyse de défaillance Française (ANADEF), Issue June 7-10 2016 Seignosse-Hossegor France, 2016

**2/3-D Device Simulations as an Effective Tool in Microelectronics Education**
*Author(s):* Aleš Chvála, Juraj Marek, Arpád Kósa, Patrik Príbytný, Ľubica Stuchlíková and Daniel Donoval

**Transfer of Knowledge from Scientific Research Projects towards Middle School Scholars**
*Author(s):* J. Kovác, jr, R. Szobolovský, A. Kósa, L. Stuchlíková and J. Kovác
*Published in:* ICETA, 2015

**Thermal Management of multifinger Power HEMTs Supported by 3-D Simulation**
*Author(s):* A. Chvála, J. Marek, P. Príbytný, J. Kováč, S. Delage, J.-C. Jacquet and D. Donoval

Peer reviewed articles (1)

Investigation of strain effects on phase diagrams in the ternary nitride alloys (InAlN, AlGaN, InGaN)

Author(s): Ranim Mohamad, Antoine Béré, Jun Chen, Pierre Ruterana

Published in: physica status solidi (a), Issue 214/9, 2017, Page(s) 1600752, ISSN 1862-6300

DOI: 10.1002/pssa.201600752

Thesis dissertations (1)

Relaxation de la contrainte dans les hétérostructures Al(Ga)InN/GaN pour applications électroniques: modélisation des propriétés physiques et rôle de l'indium dans la dégradation des couches épitaxiales

Author(s): Ranim Mohamad

Published in: 2018

Share this page

Last update: 7 October 2019
Record number: 197904

Permalink: https://cordis.europa.eu/project/id/662322/results/en

© European Union, 2019